

Substitute Form PTO-1449

U.S. Department of Commerce
Patent and Trademark Office

Attorney's Docket No.

12406-059US2

Application No.

10/625,118

**Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant

Volker Haerle

Filing Date

July 22, 2003

Group Art Unit

Unknown

2824

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
BEO	AQ	Sugano, Hikaru, "Semiconductor Laser Manufacturing Method", October 27, 1989, pp. 1-6
	AR	
	AS	
	AT	

Examiner Signature

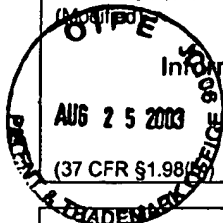
Beth E. Owens

Date Considered

2.17.04

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Other Documents (include Author, Title, Date, and Place of Publication)

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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12406-059US2	Application No. Unassigned
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(37 CFR §1.98(b))			

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Examiner Initial	Desig. ID	Document Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
BE0	AA	4,415,404	11/15/1983	Riegl			
	AB	4,614,564	09/30/1986	Sheldon et al.			
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	AJ	6,140,247	10/31/2000	Muraoka et al.			

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							Yes	No
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	AN	07202317	08/1995	JP				
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BE0	AP	JP-61 210687 Patent Abstracts of Japan, Venoffentlichung, September 8, 1986
BE0	AQ	G.B., Burns, "Lo-Temperature Native Oxide Removal From Silicon Using Nitrogen Trifluoride Prior To Low-Temperature Silicon Epitaxy", Appl. Phys. Lett. 53 (15), October 1988 pp 1423-1425
BE0	AR	T. Aoyama et al. "Silicon Surface Cleaning Using Photo excited Fluoring Gas Diluted With Hydrogen". J. Electrochem. Soc. Vol. 140, No. 6, June 1993 pp 1704-1708
BE0	AS	K. Ozasa et al., "Deposition Of Thin Indium Oxide Film and Its Application To Selective Epitaxy For In Situ Processing" Thin Solid Films, BD. 246, NR. 1/02, 1994, S. 58-64, XP000453839
BE0	AT	J.P. Harbison et al., "Tungsten Patterning As A Technique For Selective Area III-V MBE Growth", J. Vac. Sci. Technol. B3(2) March/April 1995

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Beo	AU	JP 02-046407, Patent Abstracts of Japan, Veröffentlichung: February 2, 1990, Anmeldung: August 5, 1988
Beo	AV	S. Yoshida et al., "Selective-Area Epitaxy Of GaAs Using A New Mask Material For In Situ Processes", Inst. Phys. Conf. Ser. No. 129: Chapter 3, 1992, S-49-54, XP000366199
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